

REMARKS

Claims 28-55 remain pending in this application and are presented for reconsideration.

Rejection of Claims Under 35 U.S.C. § 102

Claims 28-35 and 40-55 are rejected under 35 U.S.C. § 102(b) as being anticipated by K. Ismail, "Si/SiGe High-Speed Field Effect Transistors," IEEE IEDM Tech. Dig., pp. 509-512, 1995 ("Ismail"). Ismail appears to disclose designs for SiGe-based modulation-doped field-effect transistors. *See* Ismail, Figure 7 and related text. The Examiner relies on Ismail to teach all of the limitations of independent claims 28 and 46. However, Ismail does not teach a method of selectively removing a SiGe layer formed over a strained semiconductor layer, as recited in these claims. In fact, Ismail is utterly silent about any method utilized to form his structure of Figure 7, because he has not physically fabricated it. Figure 7 is simply a schematic of a structure existing only in circuit-performance models. *See* Ismail, p. 510, right column, bottom paragraph. The Examiner erroneously infers Applicants' method from Ismail's structure, when in fact, Ismail's structure could be fabricated in other ways. For example, rather than selectively removing layers from his N-MODFET structure (right side of Figure 7), Ismail could selectively add layers to his P-MODFET structure (left side of Figure 7).

Applicants respectfully submit that independent claims 28 and 46 and claims dependent therefrom are allowable for at least the above reasons.

Rejection of Claims Under 35 U.S.C. § 103

Claims 36-40 are rejected under 35 U.S.C. § 103(a) as being unpatentable over Ismail in view of G. K. Chang, et al., "Selective Etching of SiGe on SiGe/Si Heterostructures," J. Electrochem. Soc., Vol. 138, No. 1, 1991 ("Chang"). Applicants respectfully submit that claims 36-40 are allowable at least for the reasons for which independent claim 28, from which they depend, is allowable.

CONCLUSION

In light of the foregoing, Applicants respectfully submit that all claims are now in condition for allowance.

A check for \$180 is enclosed for the IDS fee. Applicants believe that no other fees are necessitated by the present paper. However, in the event that any additional fees are due, the Commissioner is hereby authorized to charge any such fees to Deposit Account No. 07-1700.

If the Examiner believes that a telephone conversation with Applicants' attorney would expedite allowance of this application, the Examiner is cordially invited to call the undersigned agent at (617) 570-1198.

Respectfully submitted,



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